

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a projection, the film being formed over one surface of the light-transmitting substrate;

an island-like semiconductor layer having a crystal structure covering the projection and extending over a pair of edges of the projection;

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film.

2. (Currently Amended) A semiconductor device comprising:

a light-transmitting ~~substrate and a thin film transistor over the light-transmitting~~ substrate, wherein substrate:

a base film having a projection is provided over one surface of the light-transmitting substrate;

a thin film transistor comprising:

an island-like semiconductor layer comprising a channel formation region, wherein at least a part of the channel formation region ~~of the thin film transistor~~ is provided over the projection, and wherein the island-like semiconductor layer covers the projection and extends over a pair of edges of the projection;

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film.

3. (Previously Presented) A semiconductor device according to claim 1, wherein a height of the projection is 30 to 100 nm.

4. (Previously Presented) A semiconductor device according to claim 2, wherein a height of the projection is 30 to 100 nm.

5.-10. (Canceled)

11. (Currently Amended) A semiconductor device comprising:

a light-transmitting substrate;

a base film having a region of a first thickness and a region of a second thickness ~~smaller than the first thickness, the film being formed~~ thickness, over one surface of the light-transmitting substrate, ~~[[and]] wherein the second thickness is smaller than the first thickness, and wherein an area of the region of the first thickness having an area is~~ smaller than an area of the region of the second thickness;

an island-like semiconductor layer having a crystal structure ~~over the base film, the layer being formed~~ over the region of the first thickness and the region of the second thickness,

a gate insulating film over the island-like semiconductor layer; and

a gate electrode over the gate insulating film,

wherein the island-like semiconductor layer is capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness.

12. (Currently Amended) A semiconductor device comprising:

a light-transmitting ~~substrate and a thin film transistor over the light-transmitting~~ substrate, wherein substrate;

a base film having a region of a first thickness and a region of a second thickness ~~smaller than the first thickness is provided~~ thickness, over one surface of the light-transmitting ~~substrate;~~ substrate, wherein the second thickness is smaller than the first thickness, and wherein an area of the region of the first thickness ~~has an area is~~ is smaller than ~~an area of~~ the region of the second thickness;

a thin film transistor comprising:

a channel formation region, wherein at least a part of ~~[[a]]~~ the channel formation region ~~of the thin film transistor~~ is provided over the region of the first thickness;

~~source and drain regions of the thin film transistor are provided over the projection and cover a pair of edges of the projection~~ over at least a part of the source and drain regions over the second thickness,

~~the island-like semiconductor layer is~~ wherein the channel formation region, and the source and drain regions are capable of being irradiated with light from another surface of the light-transmitting substrate through the region of the first thickness and the region of the second thickness;

a gate insulating film over ~~the island-like semiconductor layer~~ the channel formation region, and the source and drain regions; and

a gate electrode over the gate insulating film.

13. (Previously Presented) A semiconductor device according to claim 11, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

14. (Previously Presented) A semiconductor device according to claim 12, wherein a difference in film thickness between the region of the first thickness and the region of the second thickness is 30 to 100 nm.

15. (Previously Presented) A semiconductor device according to claim 1, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

16. (Previously Presented) A semiconductor device according to claim 2, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

17. (Previously Presented) A semiconductor device according to claim 11, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

18. (Previously Presented) A semiconductor device according to claim 12, wherein the base film comprises a silicon oxide film, a silicon nitride film or a silicon nitride oxide film.

19. (Previously Presented) A semiconductor device according to claim 1, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

20. (Previously Presented) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

21. (Previously Presented) A semiconductor device according to claim 11, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.

22. (Previously Presented) A semiconductor device according to claim 12, wherein the semiconductor device is applied to an electronic instrument selected from the group consisting of a personal computer, a video camera, a goggle type display, an electronic play equipment, a player using a recording medium, a digital camera, a front type projector and a rear type projector.